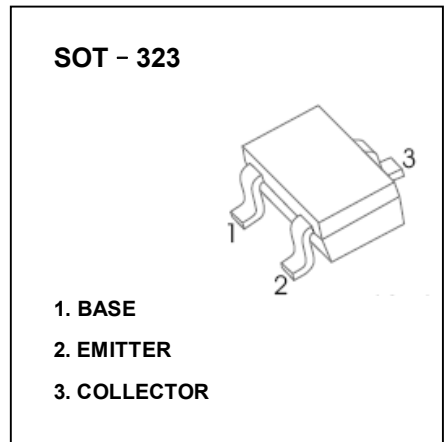


TRANSISTOR(PNP)

FEATURES

- High DC Current Gain
- High Voltage
- Complementary to 2SC4177



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-100	mA
P _C	Collector Power Dissipation	150	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	833	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE} *	V _{CE} =-6V, I _C =-1mA	90		600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Collector-emitter voltage	V _{BE}	V _{CE} =-6V, I _C =-1mA	-0.58		-0.68	V
Transition frequency	f _T	V _{CE} =-6V, I _C =-10mA		180		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		4.5		pF

*Pulse test: pulse width ≤350μs, duty cycle ≤ 2.0%.

CLASSIFICATION OF h_{FE}

RANK	M4	M5	M6	M7
RANGE	90 - 180	135 - 270	200 - 400	300 - 600
MARKING	M4	M5	M6	M7